

4496205 HITACHI/(OPTOELECTRONICS)

73C 10020 D T-39-13

2SK349, 2SK350

SILICON N-CHANNEL MOS FET**HIGH SPEED POWER SWITCHING,
HIGH FREQUENCY POWER AMPLIFIER****■ FEATURES**

- Low On-Resistance.
- High Speed Switching.
- High Cutoff Frequency.
- No Secondary Breakdown.
- Suitable for Switching Regulator, DC-DC Converter, Motor Control, and Ultrasonic Power Oscillators.

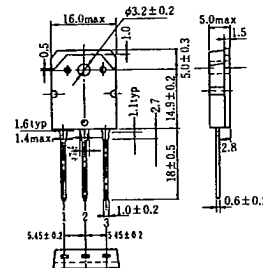
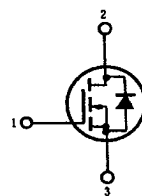
■ ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

Item	Symbol	Rating		Unit
		2SK349	2SK350	
Drain-Source Voltage	V_{DS}	400	450	V
Gate-Source Voltage	V_{GS}	± 20		V
Drain Current	I_D	10		A
Drain Peak Current	$I_{D(\text{peak})}$	15		A
Body-Drain Diode Reverse Drain Current	I_{DR}	10		A
Channel Dissipation	P_{ch}	100		W
Channel Temperature	T_{ch}	150		$^\circ\text{C}$
Storage Temperature	T_{stg}	$-55 \sim +150$		$^\circ\text{C}$

*Value at $T_c=25^\circ\text{C}$ **■ ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)**

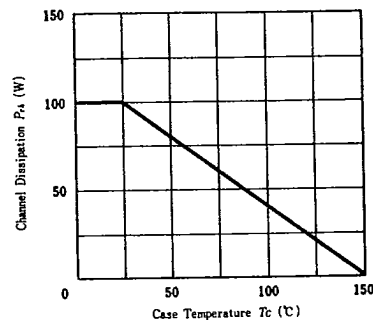
Item		Symbol	Test Condition	min.	typ.	max.	Unit
Drain-Source Breakdown Voltage	2SK349	$V_{(BR)DS}$	$I_D=10\text{mA}, V_{GS}=0$	400	—	—	V
	2SK350			450	—	—	V
Gate-Source Leak Current		I_{GS}	$V_{GS}=\pm 20\text{V}, V_{DS}=0$	—	—	± 1	μA
Zero Gate Voltage Drain Current	2SK349	I_{DSS}	$V_{DS}=320\text{V}, V_{GS}=0$	—	—	1	mA
	2SK350		$V_{DS}=360\text{V}, V_{GS}=0$	—	—	—	
Gate-Source Cutoff Voltage		$V_{GS(off)}$	$I_D=1\text{mA}, V_{DS}=10\text{V}$	1.0	—	5.0	V
Static Drain-Source On State Resistance		$R_{DS(on)}$	$I_D=5\text{A}, V_{GS}=15\text{V}^*$	—	0.67	0.9	Ω
Drain-Source Saturation Voltage		$V_{DS(sat)}$	$I_D=5\text{A}, V_{GS}=15\text{V}^*$	—	3.3	4.5	V
Forward Transfer Admittance		$ y_f $	$I_D=5\text{A}, V_{DS}=10\text{V}^*$	1.3	2.5	—	S
Input Capacitance		C_{iss}	$V_{DS}=10\text{V}, V_{GS}=0$ $f=1\text{MHz}$	—	1500	—	pF
Output Capacitance		C_{oss}		—	330	—	pF
Reverse Transfer Capacitance		C_{ris}		—	35	—	pF
Turn-on Delay Time		$t_{d(on)}$	$I_D=2\text{A}, V_{GS}=15\text{V}$ $R_L=15\Omega$	—	20	—	ns
Rise Time		t_r		—	50	—	ns
Turn-off Delay Time		$t_{d(off)}$		—	140	—	ns
Fall Time		t_f		—	60	—	ns
Body-Drain Diode Forward Voltage		V_{DF}	$I_F=5\text{A}, V_{GS}=0$	—	0.85	—	V
Body-Drain Diode Reverse Recovery Time		t_{rr}	$I_F=5\text{A}, V_{GS}=0$ $di_F/dt=100\text{A}/\mu\text{s}$	—	400	—	ns

*Pulse Test

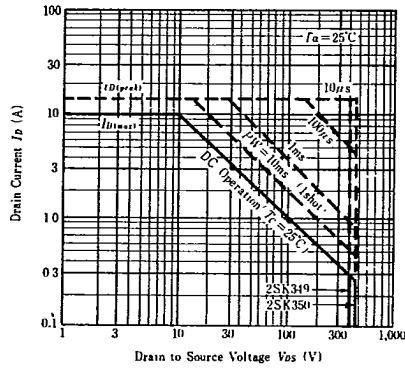


1. Gate
2. Drain
(Flange)
3. Source
(Dimensions in mm)

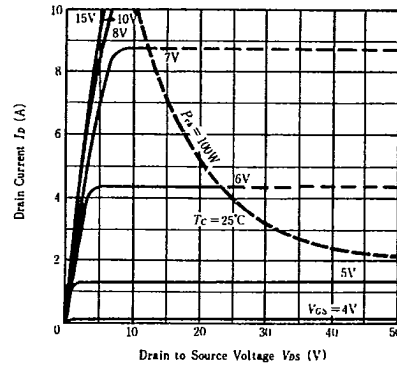
(TO-3P)

**POWER VS.
TEMPERATURE DERATING**

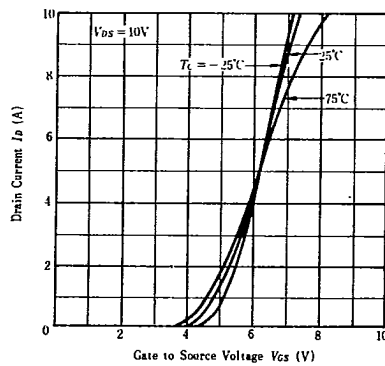
MAXIMUM SAFE OPERATION AREA



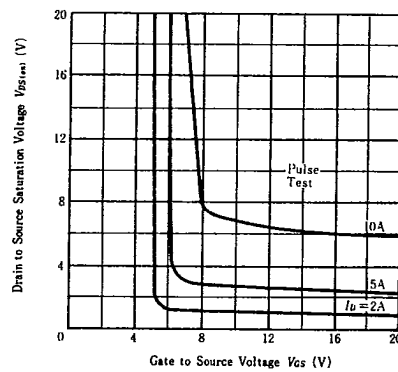
TYPICAL OUTPUT CHARACTERISTICS



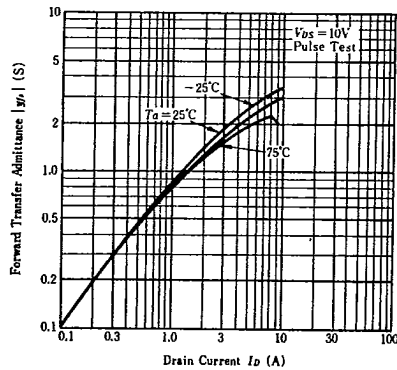
TYPICAL TRANSFER CHARACTERISTICS



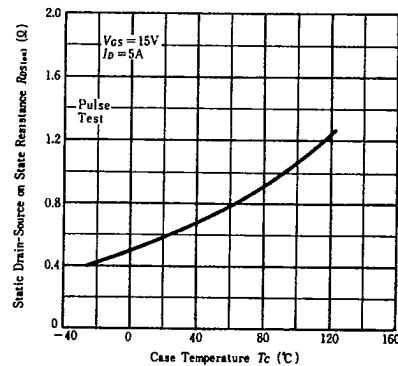
DRAIN-SOURCE SATURATION VOLTAGE VS. GATE-SOURCE VOLTAGE



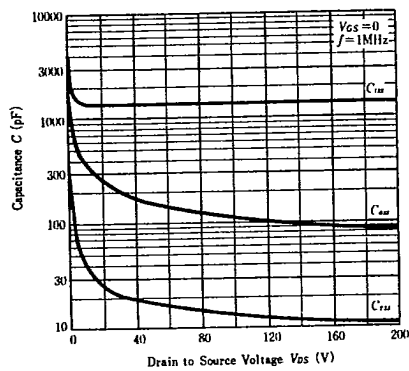
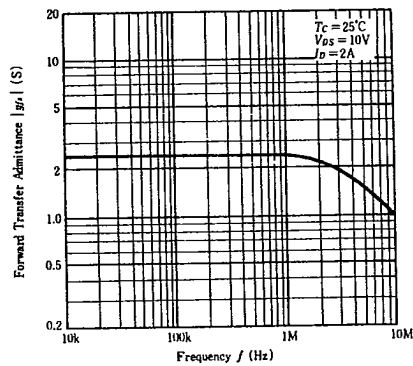
FORWARD TRANSFER ADMITTANCE VS. DRAIN CURRENT



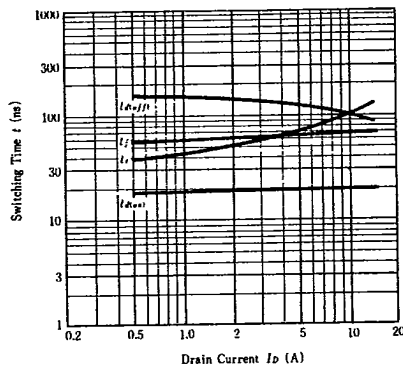
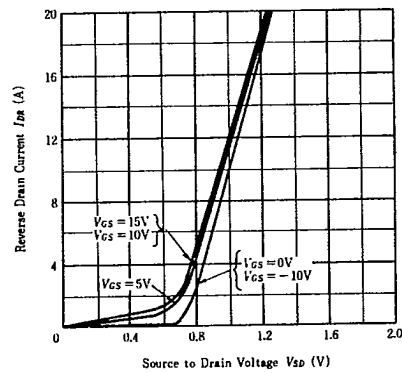
STATIC DRAIN-SOURCE ON STATE RESISTANCE VS. TEMPERATURE



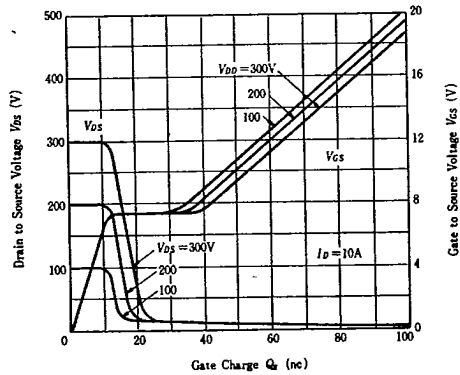
2SK349, 2SK350

TYPICAL CAPACITANCE VS.
DRAIN-SOURCE VOLTAGEFORWARD TRANSFER ADMITTANCE
VS. FREQUENCY

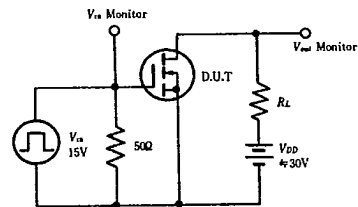
SWITCHING CHARACTERISTICS

MAXIMUM BODY-DRAIN DIODE
FORWARD VOLTAGE

DYNAMIC INPUT CHARACTERISTICS



SWITCHING TIME TEST CIRCUIT



WAVEFORMS

